

## 1.8 V to 5.5 V, 4 $\Omega$ Dual SPST Switches

### DESCRIPTION

DG723 is a precision dual SPST switch designed to operate from single 1.8 V to 5.5 V power supply with low power dissipation. The DG723 can switch both analog and digital signals within the power supply rail, and conduct well in both directions.

Fabricated with advance submicron CMOS process, the switch provides high precision low and flat ON resistance, low leakage current, low parasitic capacitance, and low charge injection.

The DG723 contains two independent Single Pole Single Throw (SPST) switches, Switch-1 is normally open and the Switch-2 is normally closed. The DG723 is of Break-Before-Make switching timing. It is packaged in MSOP8.

The DG723 is the ideal switch for use in low voltage instruments and healthcare devices, fitting the circuits of low voltage ADC and DAC, analog front end gain control, and signal path control.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The TDFN8 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free “-E4” suffix to the ordering part number. The MSOP8 package has tin device termination and is represented by “-E3”. Both device terminations meet all JEDEC standards for reflow and MSL rating.

As a further sign of Vishay Siliconix’s commitment, the DG723 is fully RoHS complaint and Halogen-free.

### FEATURES

- 1.8 V to 5.5 V single power supply
- Low and flat switch on resistance, 2.5  $\Omega$ /typ.
- Low leakage and parasitic capacitance
- > 220 MHz, - 3 dB bandwidth
- Latch-up current > 300 mA (JESD78)
- Space saving packages  
2 mm x 2 mm TDFN8  
MSOP8
- Low voltage control logic
- **Halogen-free according to IEC 61249-2-21 definition**
- **Compliant to RoHS Directive 2002/95/EC**

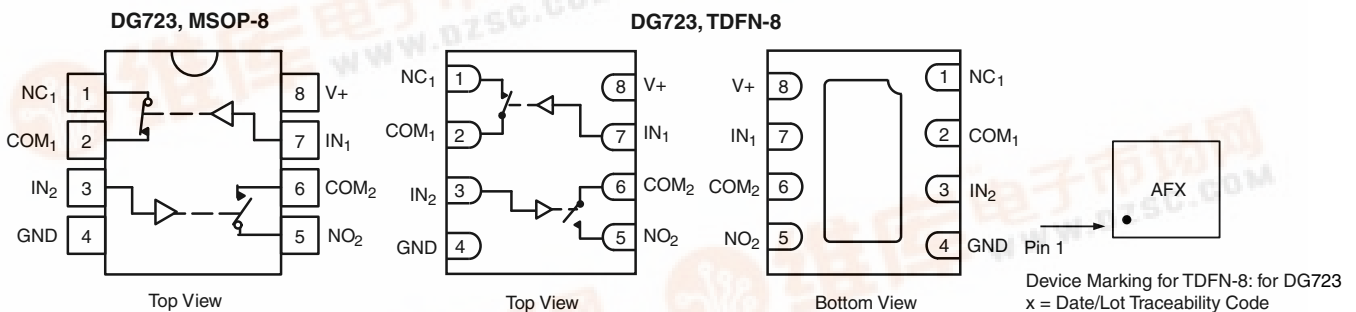


**RoHS**  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Healthcare and medical devices
- Test instruments
- Portable meters
- Data acquisitions
- Control and automation
- PDAs and modems
- Communication systems
- Audio, video systems
- Mechanical reed relay replacement

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION DG723



Device Marking for MSOP-8: 723

TRUTH TABLE DG723		
Logic	Switch-1	Switch-2
0	On	Off
1	Off	On

**ORDERING INFORMATION**

Temperature Range	Package	Part Number
- 40 °C to 85 °C	MSOP-8	DG723DQ-T1-GE3
	TDFN-8	DG723DN-T1-GE4

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Limit	Unit
Referenced V+ to GND	- 0.3 to 6.0	V
IN, COM, NC, NO <sup>a</sup>	- 0.3 to (V+ + 0.3)	
Continuous Current (Any Terminal)	± 50	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)	± 200	
Storage Temperature (D Suffix)	- 65 to 150	°C
Power Dissipation (Packages) <sup>b</sup>	MSOP-8 <sup>c</sup>	320
	TDFN-8 <sup>d</sup>	842
		mW

## Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 4.0 mW/°C above 70 °C.

d. Derate 10.53 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10 %, VIN = 0.4 or 1.5 V <sup>e</sup>	Temp. <sup>a</sup>	Limits - 40 °C to 85 °C			Unit
				Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	V
On-Resistance	R <sub>ON</sub>	V+ = 2.7 V, V <sub>COM</sub> = 0 V to V+, I <sub>NO</sub> , I <sub>NC</sub> = - 10 mA	Room Full		6.5	9	Ω
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	V+ = 2.7 V, V <sub>COM</sub> = 1.1 V to 1.6 V, I <sub>NO</sub> , I <sub>NC</sub> = - 10 mA	Room		3.3		
R <sub>ON</sub> Match <sup>d</sup>	R <sub>ON</sub> Match	V+ = 2.7 V, V <sub>D</sub> = 1.1 V to 1.6 V, I <sub>D</sub> = - 10 mA	Room Full		0.3	0.9	
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 3.3 V V <sub>NO</sub> , V <sub>NC</sub> = 1 V/3 V, V <sub>COM</sub> = 3 V/1 V	Room Full	- 0.25 - 0.35		0.25 0.35	nA
	I <sub>COM(off)</sub>		Room Full	- 0.25 - 0.35		0.25 0.35	
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 3.3 V, V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 1 V/3 V	Room Full	- 0.25 - 0.35		0.25 0.35	
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	2			V
Input Low Voltage	V <sub>INL</sub>		Full			0.4	
Input Capacitance <sup>d</sup>	C <sub>in</sub>	f = 1 MHz	Full		2.4		pF
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t <sub>ON</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 2.0 V, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF Figures 1 and 2	Room Full		16	55	ns
Turn-Off Time	t <sub>OFF</sub>		Room Full		7	40	
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	C <sub>L</sub> = 1 nF, V <sub>GEN</sub> = 0 V, R <sub>GEN</sub> = 0 Ω, Figure 3	Room		1.8		pC
Bandwidth <sup>d</sup>	BW	V+ = 3.0 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, - 3dB	Room		319		MHz
Off-Isolation <sup>d</sup>	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 1 MHz	Room		- 67		dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 92		
Off-Isolation <sup>d</sup>	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 10 MHz	Room		- 47		
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 90		
Source-Off Capacitance <sup>d</sup>	C <sub>NC/NO(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		8		pF
Drain-Off Capacitance <sup>d</sup>	C <sub>COM(off)</sub>		Room		9		
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		22		
Power Supply							
Power Supply Current	I+	V <sub>IN</sub> = 0 or V+, V+ = 3.3 V				1.0	μA

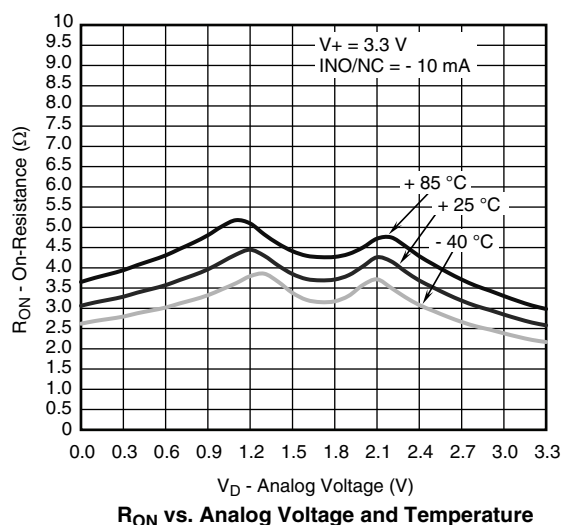
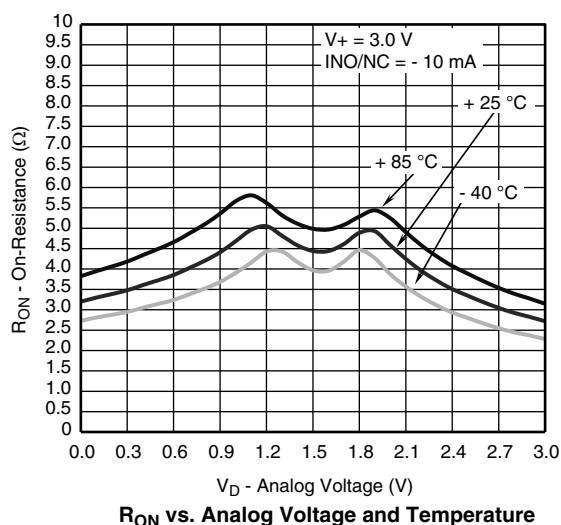
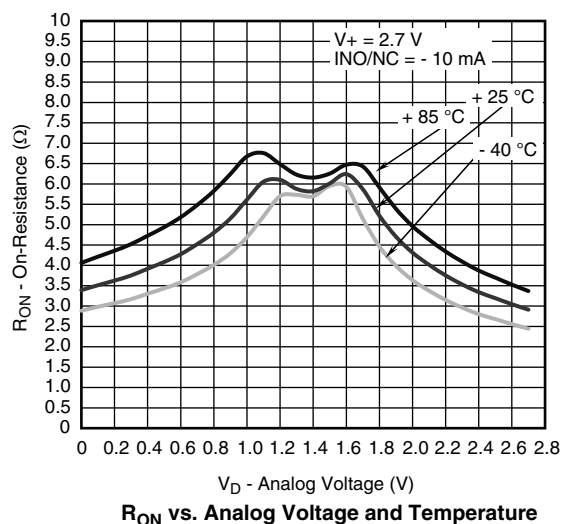
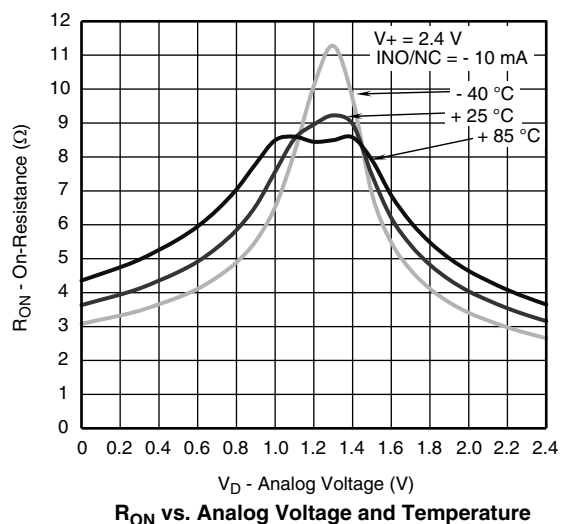
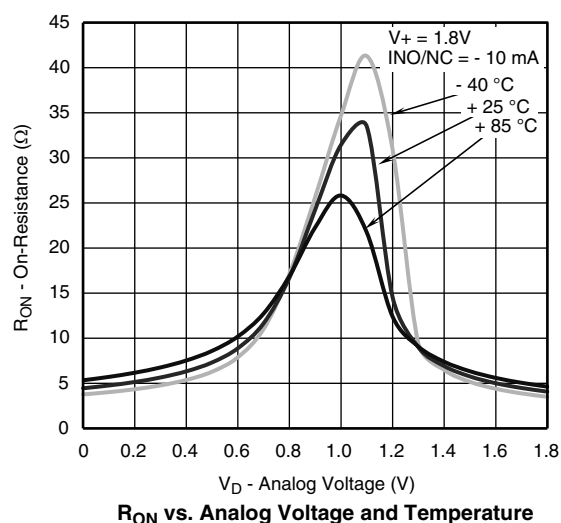
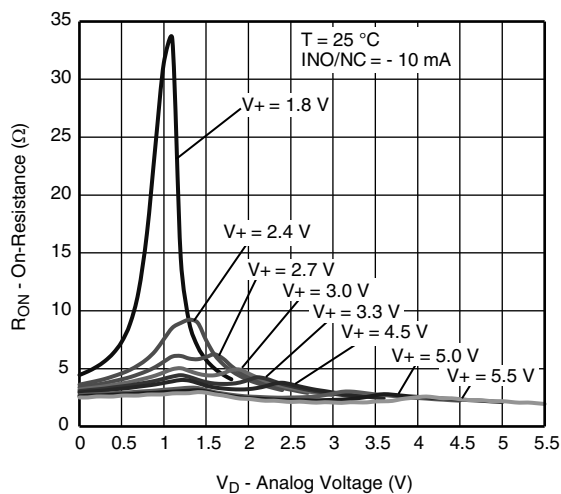
SPECIFICATIONS (V+ = 5.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5 V, ± 10 %, V <sub>IN</sub> = 0.8 or 2.4 V <sup>e</sup>	Temp. <sup>a</sup>	Limits - 40 °C to 85 °C			Unit
				Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	V
On-Resistance	R <sub>ON</sub>	V+ = 4.5 V, V <sub>COM</sub> = 0 V to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full		2.5	4.5 5	Ω
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	V+ = 4.5 V, V <sub>COM</sub> = 1.3 V to 3.0 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room		0.85	1.5	
R <sub>ON</sub> Match <sup>d</sup>	R <sub>ON</sub> Match	V+ = 4.5 V, I <sub>D</sub> = 10 mA, V <sub>COM</sub> = 1.3 V to 3.0 V	Room		0.2	0.9	
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 5.5 V V <sub>NO</sub> , V <sub>NC</sub> = 1 V/4.5 V, V <sub>COM</sub> = 4.5 V/1 V	Room Full	- 0.25 - 0.35		0.25 0.35	nA
	I <sub>COM(off)</sub>		Room Full	- 0.25 - 0.35		0.25 0.35	
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 5.5 V V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 1 V/4.5 V	Room Full	- 0.25 - 0.35		0.25 0.35	
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	2.4			V
Input Low Voltage	V <sub>INL</sub>		Full			0.8	
Input Capacitance	C <sub>in</sub>	f = 1 MHz	Full		2.2		pF
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	- 0.1	0.005	0.1	μA
Dynamic Characteristics							
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 3 V, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF Figures 1 and 2	Room Full		17	30 40	ns
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>		Room Full		9	35	
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	C <sub>L</sub> = 1 nF, V <sub>GEN</sub> = 0 V, R <sub>GEN</sub> = 0 Ω, Figure 3	Room		2.2		pC
Bandwidth <sup>d</sup>	BW	V+ = 5 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, - 3 dB	Room		366		MHz
Off-Isolation <sup>d</sup>	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 1 MHz	Room		- 67		dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 90		
Off-Isolation <sup>d</sup>	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 10 MHz	Room		- 47		
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 90		
Source-Off Capacitance <sup>d</sup>	C <sub>NC/NO(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		8		pF
Drain-Off Capacitance <sup>d</sup>	C <sub>COM(off)</sub>		Room		9		
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		22		
Power Supply							
Power Supply Range	V+			2.6		4.3	V
Power Supply Current	I+	V <sub>IN</sub> = 0 or V+, V+ = 5.5 V	Full			2	μA

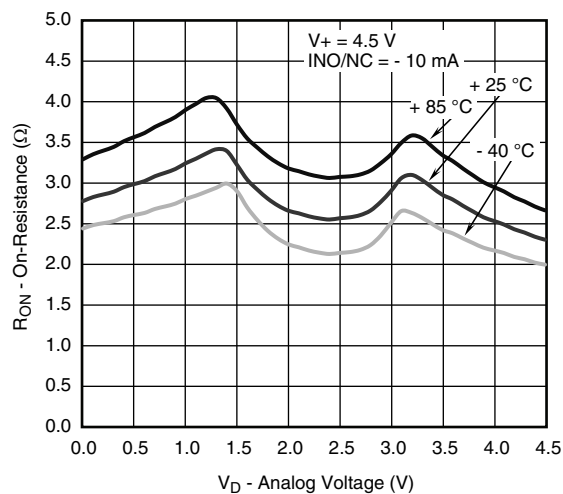
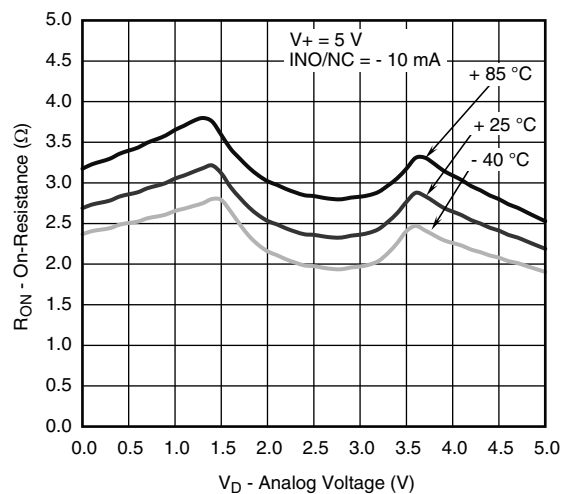
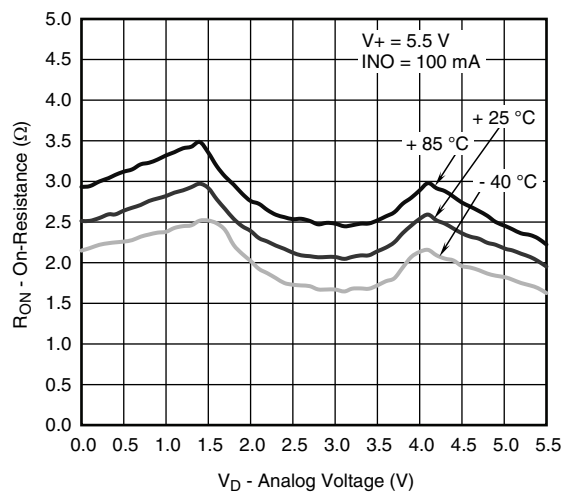
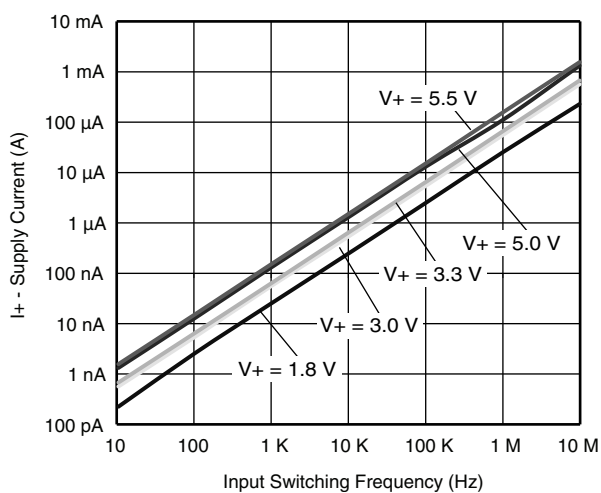
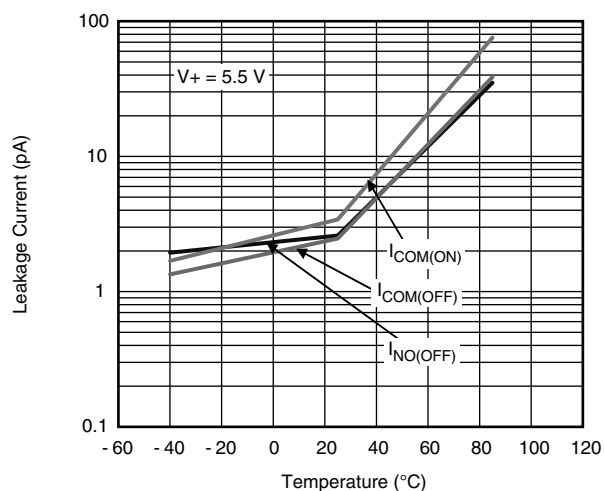
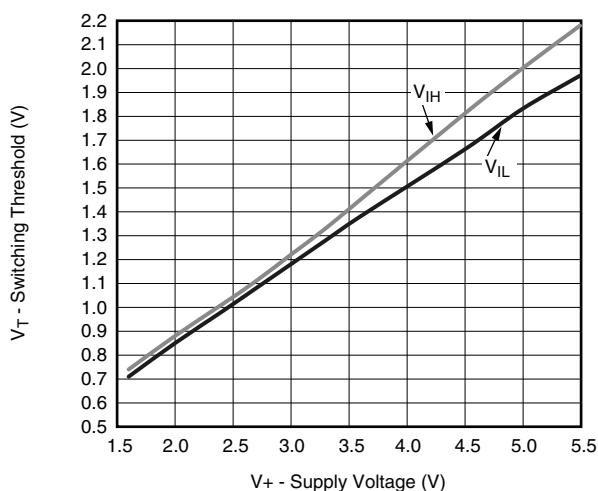
## Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.  
b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.  
c. Typical values are for design aid only, not guaranteed nor subject to production testing.  
d. Guarantee by design, nor subjected to production test.  
e. V<sub>IN</sub> = input voltage to perform proper function.  
f. Not production tested.

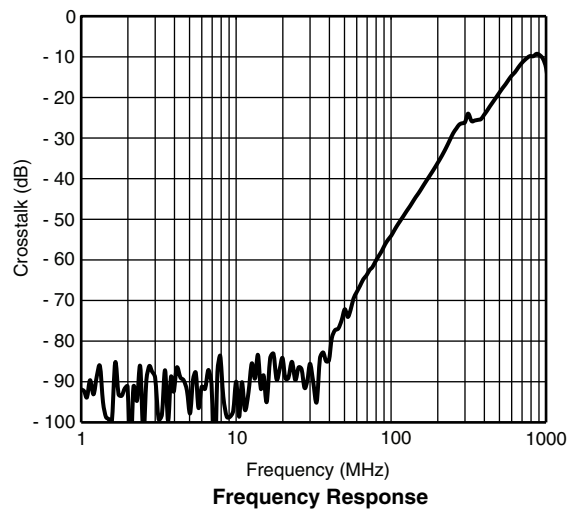
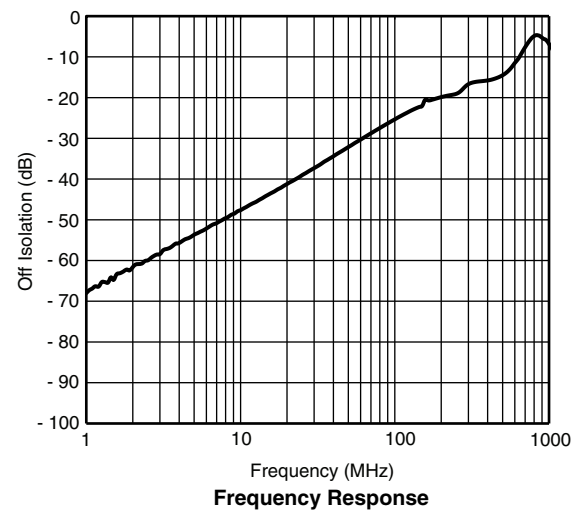
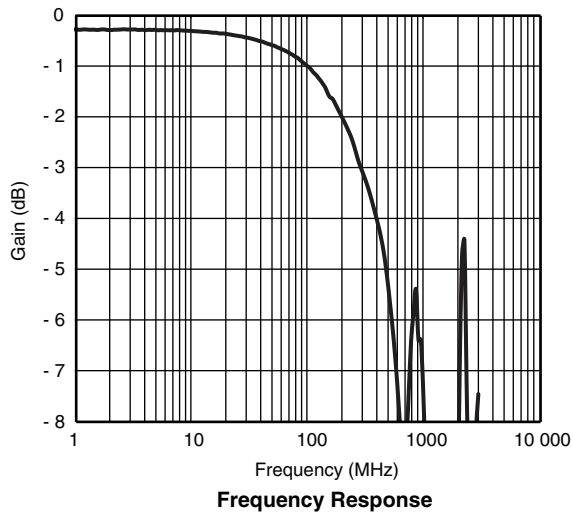
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

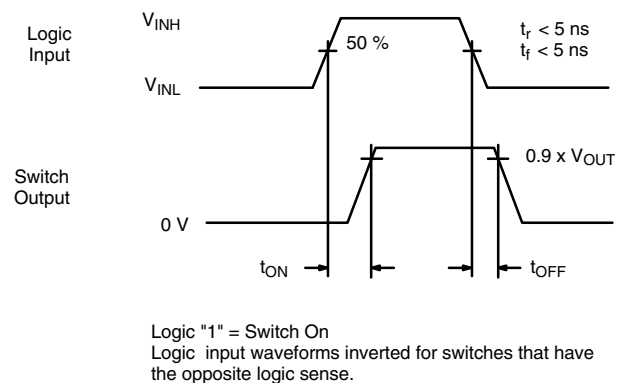
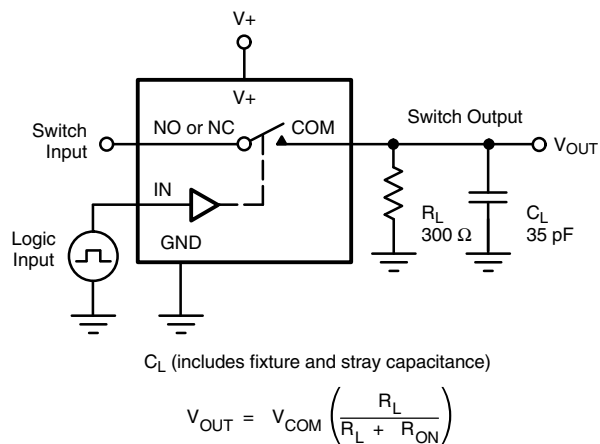


**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

 **$R_{ON}$  vs. Analog Voltage and Temperature**

 **$R_{ON}$  vs. Analog Voltage and Temperature**

 **$R_{ON}$  vs. Analog Voltage and Temperature**

**Supply Current vs. Input Switching Frequency**

**Leakage Current vs. Temperature**

**Switching Threshold vs. Supply Voltage**

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

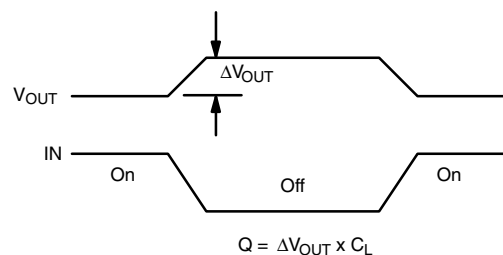
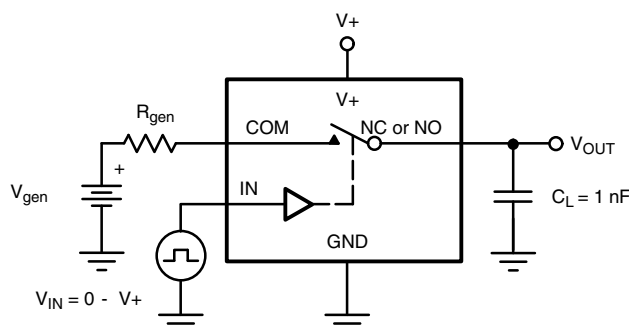


**TEST CIRCUITS**



**Figure 1. Switching Time**

## TEST CIRCUITS



IN depends on switch configuration: input polarity determined by sense of switch.

Figure 2. Charge Injection

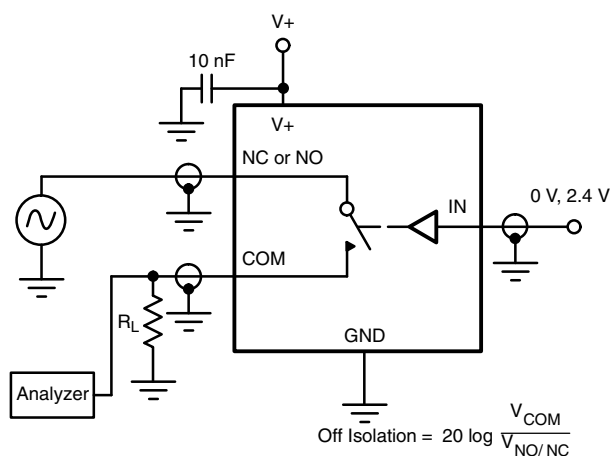


Figure 3. Off-Isolation

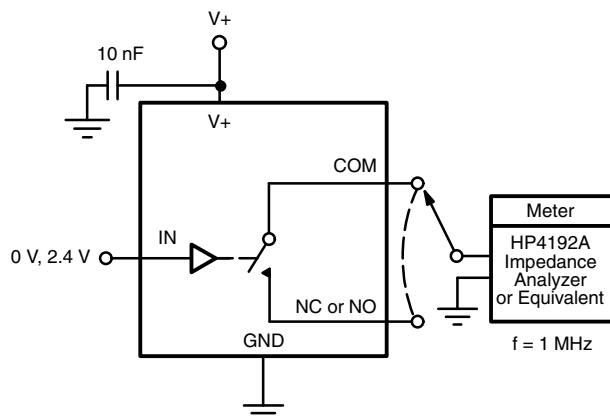


Figure 4. Channel Off/On Capacitance

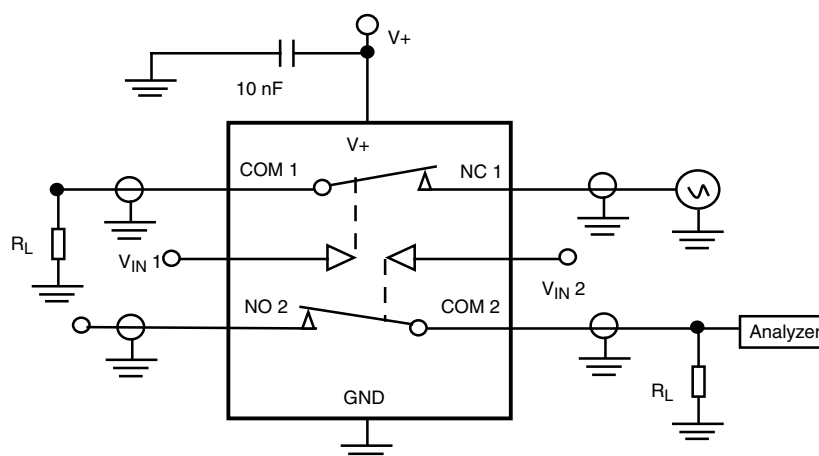


Figure 5. Channel to Channel Crosstalk

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